



### 20V Complementary Enhancement Mode MOSFET - ESD Protected

Voltage

20 / -20V

Current

1 / -0.7A

#### **Features**

#### **Application**

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected
- Lead free in comply with EU RoHS 2011/65/EU directives.
- Green molding compound as per IEC61249 Std. (Halogen Free)

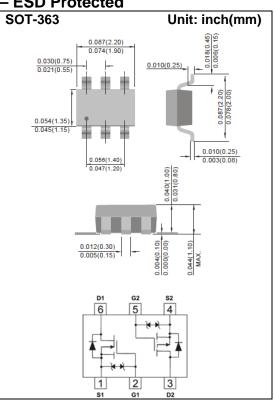
#### **Mechanical Data**

• Case: SOT-363 Package

• Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0002 ounces, 0.006 grams

• Marking: T60



# **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage		$V_{DS}$	20 -20		V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 8 <u>+</u> 8		>
Continuous Drain Current		I <sub>D</sub>	1	-0.7	Α
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	4	-2.8	Α
B	T <sub>a</sub> =25°C	-	350		mW
Power Dissipation	Derate above 25°C	$P_{D}$	2	mW/°C	
Operating Junction and Storage Tem	$T_{J}, T_{STG}$	-55~150		°C	
Thermal resistance					
- Junction to Ambient (Note 3)		$R_{\theta JA}$	357		°C/W

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# **N-Channel Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> = 250uA	20	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	0.7	0.8	1.1	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ = 4.5V, $I_{D}$ = 1A	-	114	150	mΩ
		$V_{GS}$ = 2.5V, $I_{D}$ = 0.7A	-	160	215	
		$V_{GS}$ = 1.8V, $I_{D}$ = 0.3A	-	280	400	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> =0V	-	0.01	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	<u>+</u> 2	<u>+</u> 10	uA
Dynamic						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V, I <sub>D</sub> =1A, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	1.6	-	nC
Gate-Source Charge	$Q_gs$		-	0.3	-	
Gate-Drain Charge	$Q_gd$		-	0.41	-	
Input Capacitance	Ciss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	105	-	
Output Capacitance	Coss		-	25	-	pF
Reverse Transfer Capacitance	Crss		-	15	-	
Switching						
Turn-On Delay Time	td <sub>(on)</sub>	\/ -40\/ I -4A	-	5.8	-	
Turn-On Rise Time	tr	$V_{DD}$ =10V, $I_{D}$ =1A, $V_{GS}$ =4.5V, $R_{G}$ =6 $\Omega$ (Note 1,2)		25.7	-	
Turn-Off Delay Time	td <sub>(off)</sub>			41	-	ns
Turn-Off Fall Time	tf		-	31	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	1	Α
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1A, V <sub>GS</sub> =0V		0.85	1.2	V

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## **P-Channel Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> = -250uA	-20	-	i	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250uA$	-0.5	-0.64	-1	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ = -4.5V, $I_{D}$ = -0.7A	-	260	325	mΩ
		$V_{GS}$ = -2.5V, $I_{D}$ = -0.6A	-	310	420	
		$V_{GS}$ = -1.8V, $I_{D}$ = -0.5A	-	400	600	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	-	-0.01	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	<u>+</u> 3.5	<u>+</u> 10	uA
Dynamic						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =-10V, I <sub>D</sub> =-0.7A, V <sub>GS</sub> =-4.5V (Note 1,2)	-	2.2	-	nC
Gate-Source Charge	$Q_gs$		-	0.4	ı	
Gate-Drain Charge	$Q_{gd}$		-	0.5	i	
Input Capacitance	Ciss	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	165	i	pF
Output Capacitance	Coss		-	25	i	
Reverse Transfer Capacitance	Crss		-	14.7	i	
Switching						
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =-10V, $I_{D}$ =-0.7A, $V_{GS}$ =-4.5V, $R_{G}$ =6 $\Omega$ (Note 1,2)	-	8.9	ı	
Turn-On Rise Time	tr			37	-	
Turn-Off Delay Time	td <sub>(off)</sub>			127	ı	ns
Turn-Off Fall Time	tf		-	70	ı	
Drain-Source Diode						
Maximum Continuous Drain-Source	1_	I <sub>S</sub>	_	_	-1	А
Diode Forward Current	'5					
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.86	-1.2	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ROJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.





#### **N-Channel TYPICAL CHARACTERISTIC CURVES**

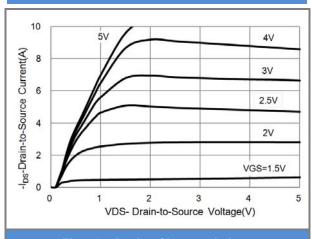
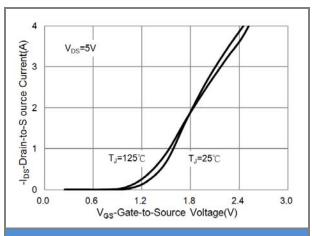


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

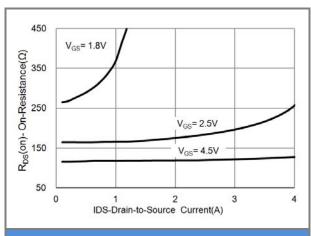


Fig.3 On-Resistance vs. Drain Current

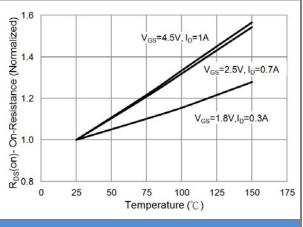


Fig.4 On-Resistance vs. Junction temperature

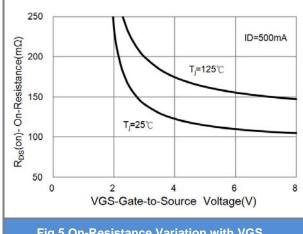
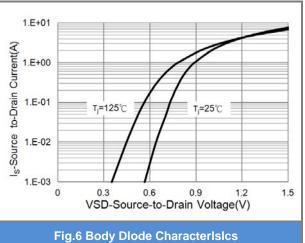


Fig.5 On-Resistance Variation with VGS.







#### N-Channel TYPICAL CHARACTERISTIC CURVES

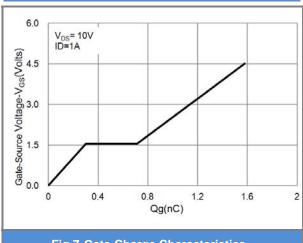


Fig.7 Gate-Charge Characteristics

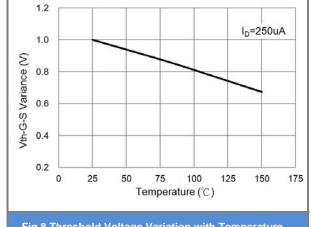


Fig.8 Threshold Voltage Variation with Temperature.

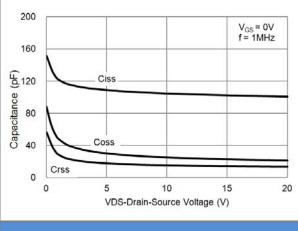


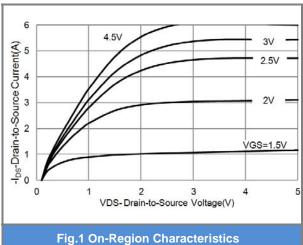
Fig.9 Capacitance vs. Drain-Source Voltage.

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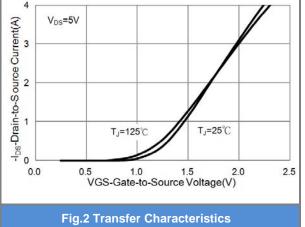




#### P-Channel TYPICAL CHARACTERISTIC CURVES



0



V<sub>GS</sub>=4.5V, I<sub>D</sub>=0.7A

V<sub>GS</sub>=1.8V, I<sub>D</sub>=0.5A

100

Temperature (°C)

125

150

175

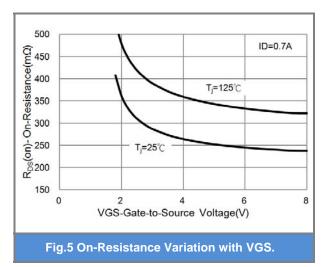
500 V<sub>GS</sub>= 1.8V V<sub>GS</sub>= 2.5V V<sub>GS</sub>= 4.5V 200 0 2 IDS-Drain-to-Source Current(A)

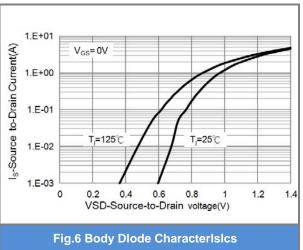


50

75

25

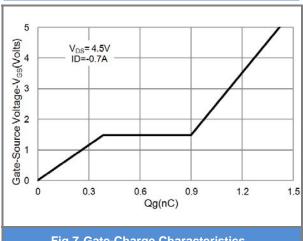








#### P-Channel TYPICAL CHARACTERISTIC CURVES



**Fig.7 Gate-Charge Characteristics** 

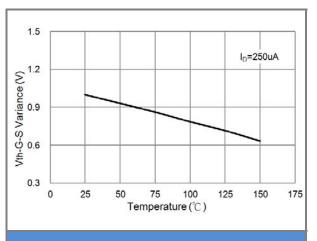


Fig.8 Threshold Voltage Variation with Temperature.

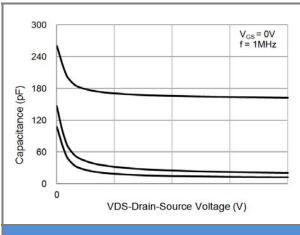


Fig.9 Threshold Voltage Variation with Temperature.

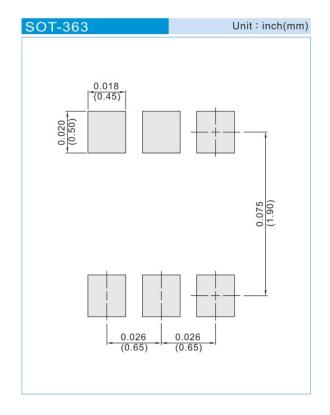




#### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJT7600_R1_00001	SOT-363	3K pcs / 7" reel	T60	Halogen free
PJT7600_R2_00001	SOT-363	10K pcs / 13" reel	T60	Halogen free

### **MOUNTING PAD LAYOUT**







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